

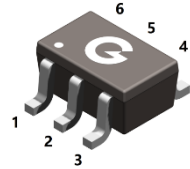
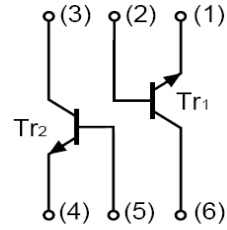
Features

- Epitaxial planar die construction
- Two chips in a package
- Transistor elements are independent, eliminating interference
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: SOT-363
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOT-363

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
UMX1N	SOT-363	3000 pcs / Tape & Reel	X1

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V_{CBO}	60	V
Collector-Emitter Breakdown Voltage	V_{CEO}	50	V
Emitter-Base Breakdown Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	150	mA
Peak Collector Current	I_{CM}	200	mA

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation($T_A = 25^\circ\text{C}$)	P_D	150	mW
Thermal Resistance Junction-to-Air ^{*1}	$R_{\theta JA}$	380	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case ^{*1}	$R_{\theta JC}$	280	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Lead ^{*1}	$R_{\theta JL}$	300	$^\circ\text{C/W}$
Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu\text{A}, I_E = 0$	60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}, I_C = 0$	7	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60\text{V}, I_E = 0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7\text{V}, I_C = 0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	110	-	630	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	0.4	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	1.2	V
Transition Frequency	f_T	$I_C = 2\text{mA}, V_{CE} = 12\text{V}$ $f = 100\text{MHz}$	-	180	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	-	3.5	pF

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

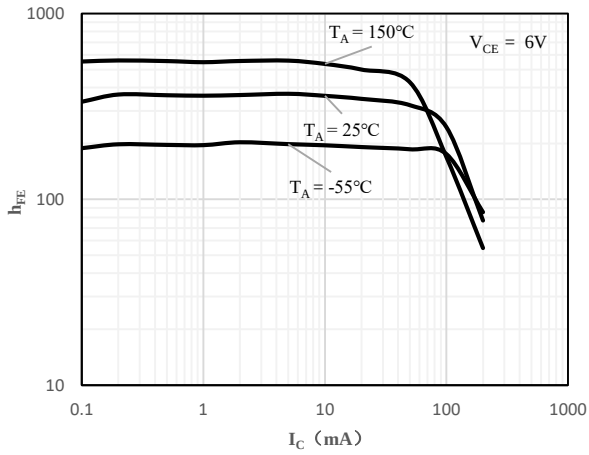


Fig 1 h_{FE} vs. I_C

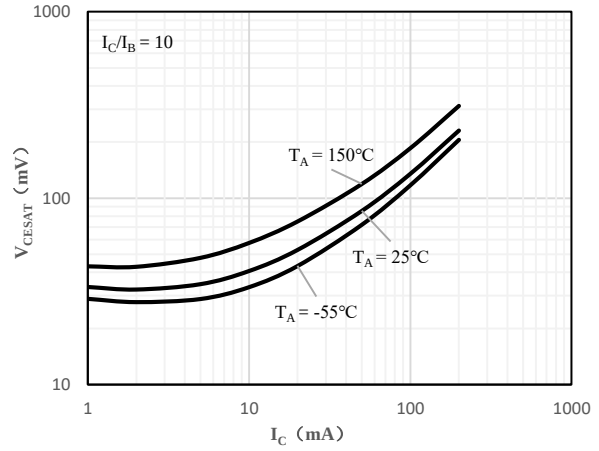


Fig 2 $V_{CE(sat)}$ vs. I_C

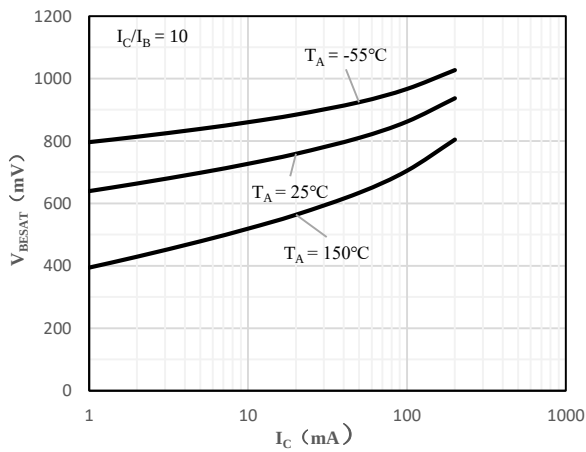


Fig 3 $V_{BE(sat)}$ vs. I_C

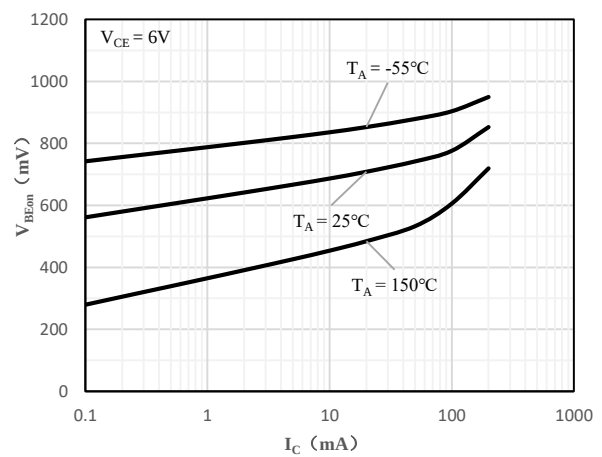


Fig 4 $V_{BE(on)}$ vs. I_C

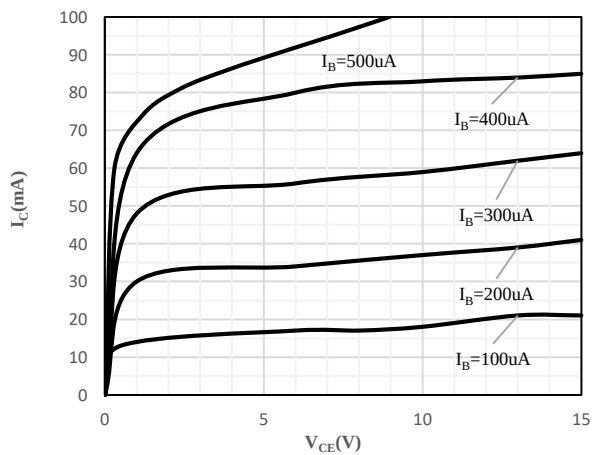


Fig 5 I_C vs. V_{CE}

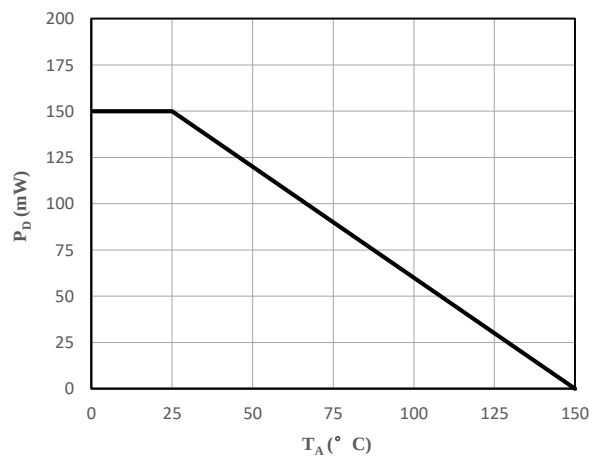


Fig 6 P_D vs. T_A

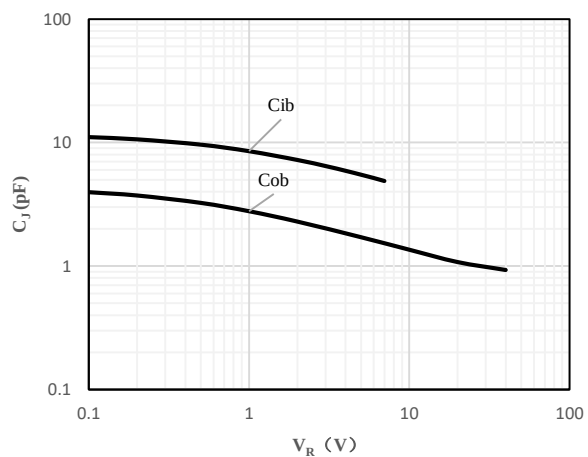
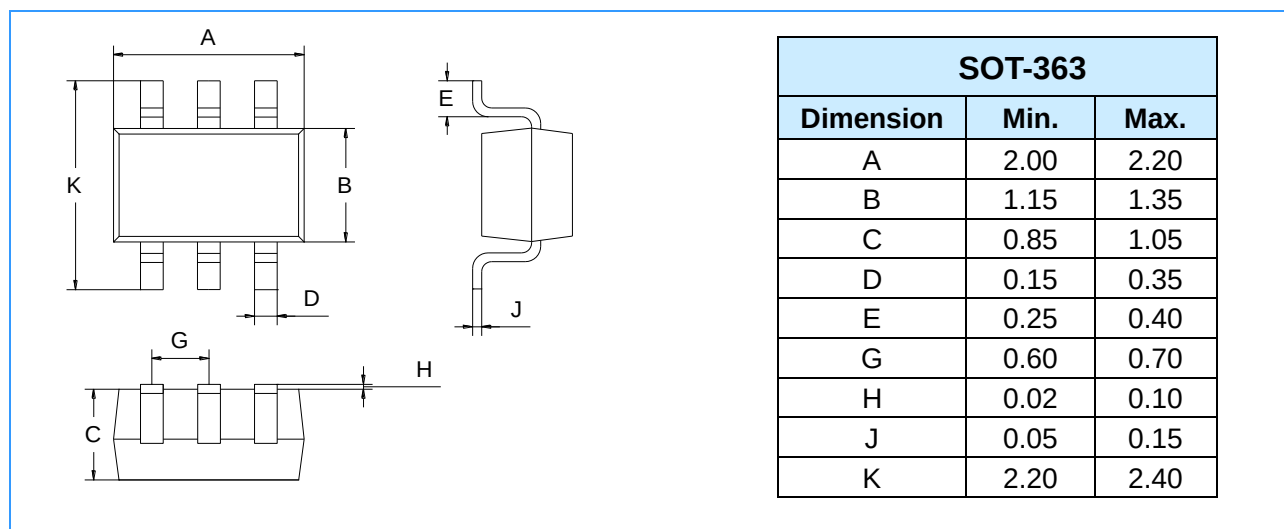


Fig 7 C_J vs. V_R

Package Outline Dimensions (Unit: mm)



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